

<b>L Number</b>	<b>Hits</b>	<b>Search Text</b>	<b>DB</b>	<b>Time stamp</b>
<b>214</b>	<b>0</b>	<b>(tft or (thin near film near transistor)) with drain with electrode with source with gate with (semiconductor adj layer) with (aluminum or alumina) with titanium with (preventive or preventing)</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2004/09/29 15:39</b>
<b>215</b>	<b>0</b>	<b>(tft or (thin near film near transistor)) same drain same electrode same source same gate same (semiconductor adj layer) same (aluminum or alumina) same titanium same (diffusion adj (preventive or preventing))</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2004/09/29 15:40</b>
<b>216</b>	<b>0</b>	<b>(tft or (thin near film near transistor)) same drain same electrode same source same gate same (semiconductor adj layer) same (aluminum or alumina) same titanium same (diffusion adj (preventive or prevention or preventing))</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2004/09/29 15:41</b>
<b>217</b>	<b>719</b>	<b>(tft or (thin near film near transistor)).clm. and (((source adj electrode) or (drain adj electrode) and (gate adj electrode)) with aluminum)</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2004/09/29 15:42</b>
<b>218</b>	<b>1</b>	<b>(tft or (thin near film near transistor)).clm. and (((source adj electrode) or (drain adj electrode) and (gate adj electrode)) with aluminum with titanium with (diffusion adj (preventing or prevention or preventive)))</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2004/09/29 15:44</b>
<b>219</b>	<b>1</b>	<b>(tft or (thin near film near transistor)).clm. and (((source adj electrode) or (drain adj electrode) and (gate adj electrode)) with aluminum with titanium with (diffusion adj (preventing or prevention or preventive))).clm.</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2004/09/29 15:45</b>